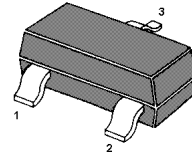
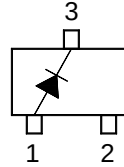


SDB789

Silicon Epitaxial Planar Schottky Barrier Diode

For small current rectification and switching applications



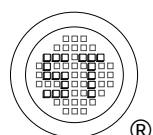
Marking Code: **M3W**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	60	V
DC Reverse Voltage	V_R	60	V
Average Forward Current	$I_{F(AV)}$	500	mA
Peak Forward Surge Current (10 ms)	I_{FSM}	2	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 500\text{ mA}$	V_F	-	0.65	V
Reverse Current at $V_R = 50\text{ V}$	I_R	-	100	μA
Terminal Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_t	60	-	pF



Dated : 02/07/2009

